



SURFACE MOUNT GLASS PASSIVATED RECTIFIER

ES1A THRU ES1J

VOLTAGE RANGE
CURRENT

50 to 600 Volts
1.0 Ampere

FEATURES

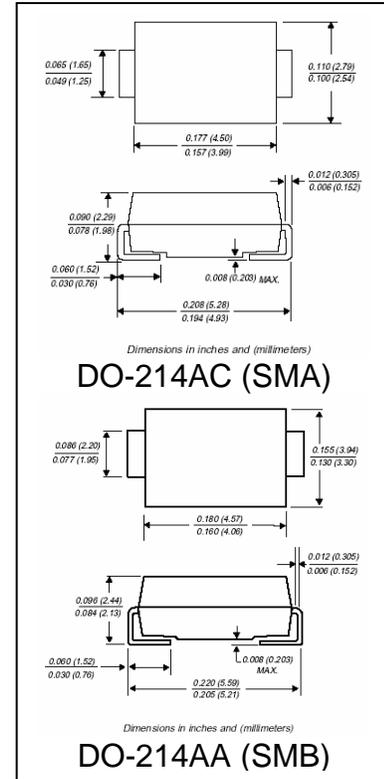
- Plastic package has UL flammability classification 94V-0
- Glass passivated chip junction
- Built in strain relief
- Super Fast switching speed for high efficiency
- High temperature Soldering guaranteed: 260 °C / 10 seconds
- Also available in the SMB package, add suffix B, i.e. ES1AB

MECHANICAL DATA

- Case: Transfer molded plastic
- Terminals: Solder plated, solderable per MIL-STD 750, Method 2026
- Polarity: Color band denotes cathode end
- Weight: 0.002 ounce, 0.064 gram – DO-214C (SMA)
0.003 ounce, 0.093 gram – DO-214AA (SMB)

MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

- Ratings at 25°C ambient temperature unless otherwise specified
- Single Phase, half wave, 60Hz, resistive or inductive load
- For capacitive load derate current by 20%



| | SYMBOLS | ES1A | ES1B | ES1C | ES1D | ES1F | ES1G | ES1J | UNIT |
|--|-----------------|-------------------|------|------|------|------|------|------|--------------------|
| Maximum Repetitive Peak Reverse Voltage | V_{RRM} | 50 | 100 | 150 | 200 | 300 | 400 | 600 | Volts |
| Maximum RMS Voltage | V_{RMS} | 35 | 70 | 105 | 140 | 210 | 280 | 420 | Volts |
| Maximum DC Blocking Voltage | V_{DC} | 50 | 100 | 150 | 200 | 300 | 400 | 600 | Volts |
| Maximum Average Forward Rectified Current, At $T_J = 100^\circ\text{C}$ (Note 1) | $I_{(AV)}$ | 1.0 | | | | | | | Amps |
| Peak Forward Surge Current 8.3ms single half sine wave superimposed on rated load (JEDEC method) | I_{FSM} | 30 | | | | | | | Amps |
| Maximum Instantaneous Forward Voltage @ 1.0A | V_F | 0.95 | | | 1.25 | | 1.7 | | Volts |
| Maximum DC Reverse Current at Rated $T_A = 25^\circ\text{C}$ | I_R | 5.0 | | | | | | | μA |
| DC Blocking Voltage per element $T_A = 125^\circ\text{C}$ | | 100 | | | | | | | |
| Maximum Reverse Recovery Time Test conditions $I_F = 0.5\text{A}$, $I_R = 1.0\text{A}$, $I_{RR} = 0.25\text{A}$ | t_{rr} | 35 | | | | | | | nS |
| Typical Junction Capacitance (Measured at 1.0MHz and applied reverse voltage of 4.0V) | C_J | 10 | | | | 8 | | | pF |
| Typical Thermal Resistance (Note 1) | $R_{\theta JA}$ | 88 (SMA) 75 (SMB) | | | | | | | $^\circ\text{C/W}$ |
| | $R_{\theta JL}$ | 28 (SAM) 17 (SMB) | | | | | | | |
| Operating Junction Temperature Range | T_J | (-55 to +150) | | | | | | | $^\circ\text{C}$ |
| Storage Temperature Range | T_{STG} | (-55 to +150) | | | | | | | $^\circ\text{C}$ |

Notes:

1. Thermal resistance from junction to ambient and from junction to lead mounted on PCB with 0.2" x 0.2" (5.0 x 5.0mm) copper pad areas.



RATINGS AND CHARACTERISTIC CURVES ES1A THRU ES1J

FIG.1-TYPICAL FORWARD CURRENT DERATING CURVE

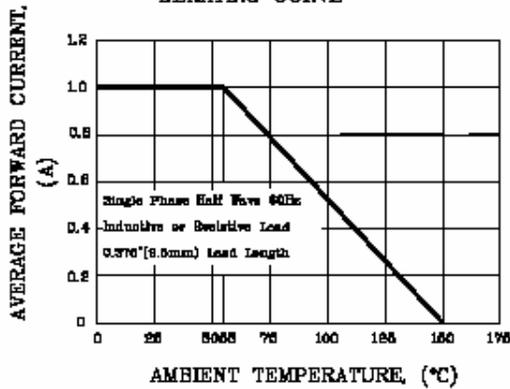


FIG.2-MAXIMUM NON-REPETITIVE PEAK FORWARD SURGE CURRENT

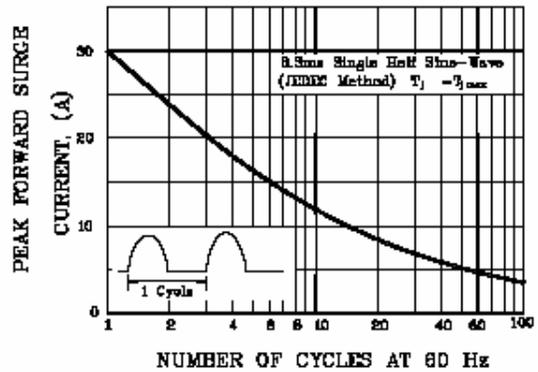


FIG.3-TYPICAL INSTANTANEOUS FORWARD CHARACTERISTICS

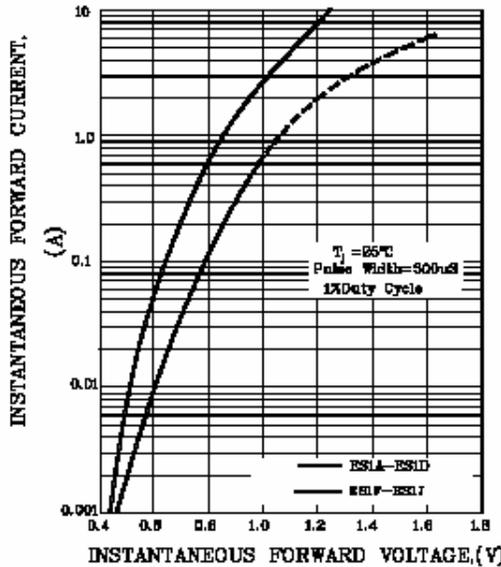


FIG.4-TYPICAL REVERSE CHARACTERISTICS

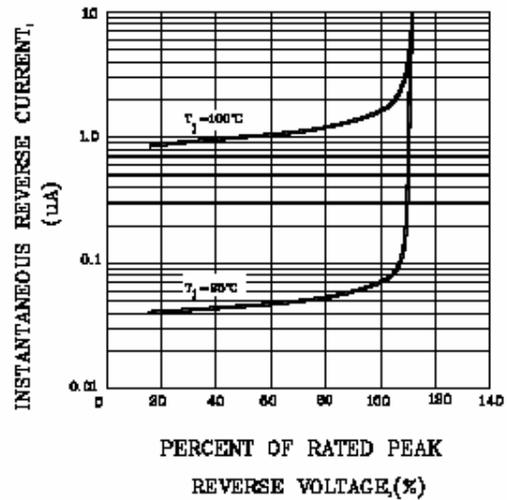


FIG.5-TYPICAL JUNCTION CAPACITANCE

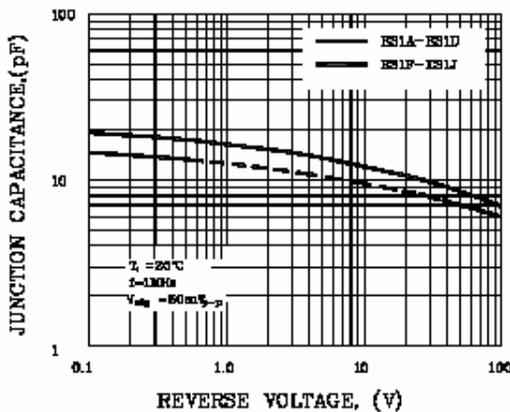
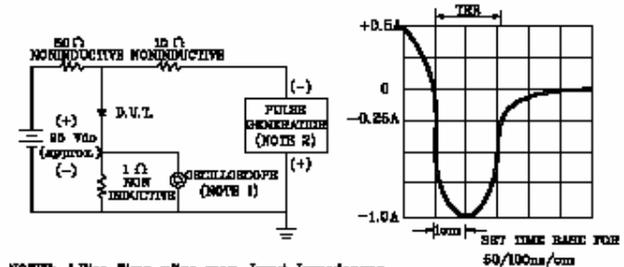


FIG.6-TEST CIRCUIT DIAGRAM AND REVERSE RECOVERY TIME CHARACTERISTIC



NOTES: 1.Rise Time = 7ns max. Input Impedance = 1 megohm. 22pF
 2.Rise time = 10ns max. Source Impedance = 60 ohms